



UNI-SEMICONDUCTOR CO., LTD

宇力半导体有限公司



AP25P06K Data Sheet

V 1.1

版权归宇力半导体有限公司

Description

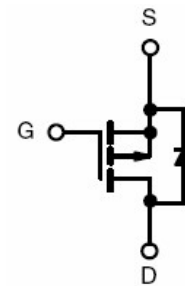
The AP25P06K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for high current load applications.

General Features

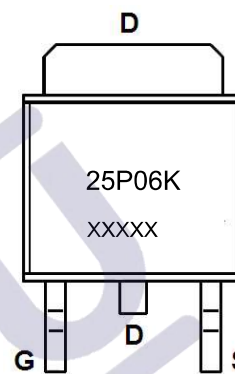
- $V_{DS} = -60V, I_D = -25A$
 $R_{DS(ON)} < 60m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 72m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low $R_{ds(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

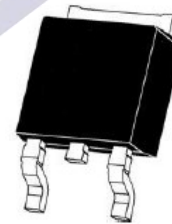
- High side switch for full bridge converter
- DC/DC converter for LCD display



Schematic diagram



Marking and pin assignment



TO-252 -2L top view

Package Marking and Ordering Information

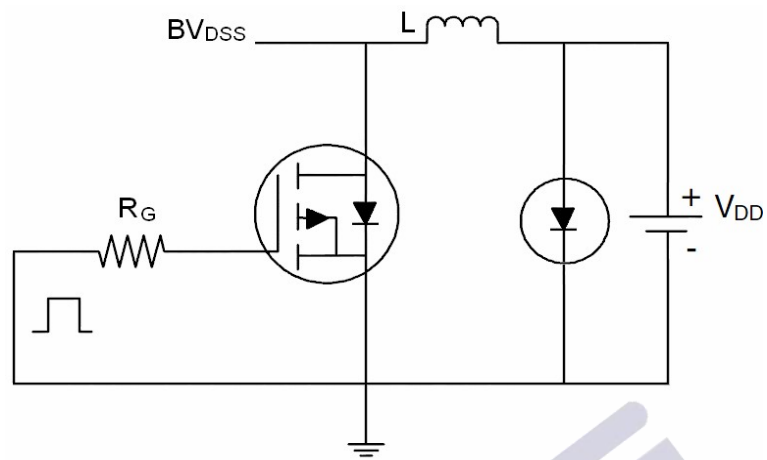
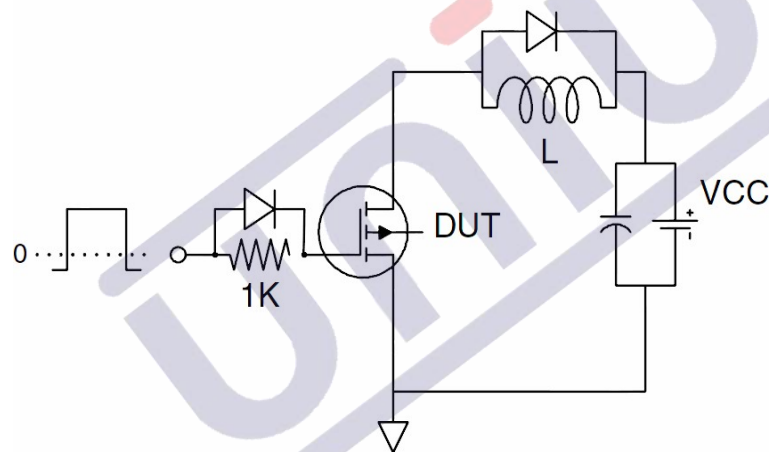
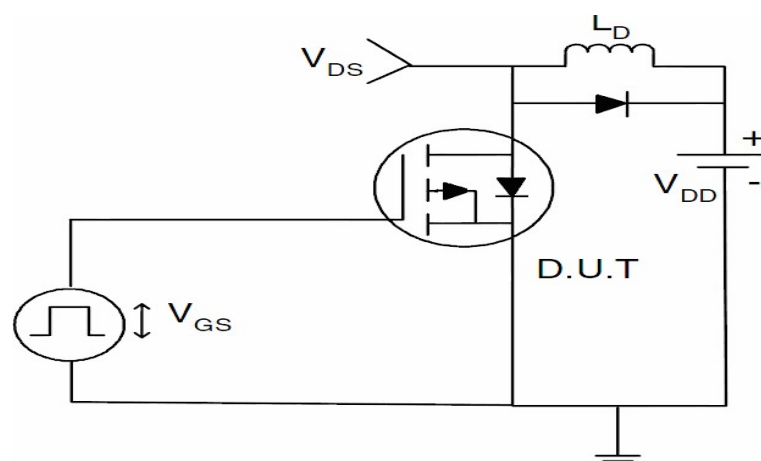
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
25P06K	AP25P06K	TO-252			

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-25	A
Drain Current-Continuous ($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-12.7	A
Pulsed Drain Current	I_{DM}	-72	A
Maximum Power Dissipation	P_D	60	W
Derating factor		0.4	$W/^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	50	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.5	$^\circ C/W$
--	-----------------	-----	--------------

Test Circuit**1) E_{AS} Test Circuit****2) Gate Charge Test Circuit****3) Switch Time Test Circuit**

1.版本记录

DATE	REV.	DESCRIPTION
2018/04/19	1.0	First Release
2021/11/12	1.1	Layout adjustment

2.免责声明

浙江宇力微新能源科技有限公司保留对本文档的更改和解释权力，不另行通知! 客户在下单前应获取我司最新版本资料，并验证相关信息是否最新和完整。量产方案需使用方自行验证并自担所有批量风险责任。未经我司授权，该文件不得私自复制和修改。产品不断提升，以追求高品质、稳定性强、可靠性高、环保、节能、高效为目标，我司将竭诚为客户提供性价比高的系统开发方案、技术支持等更优秀的服务。

版权所有 浙江宇力微新能源科技有限公司/绍兴宇力半导体有限公司

3.联系我们

浙江宇力微新能源科技有限公司

总部地址：绍兴市越城区斗门街道袍渎路25号中节能科创园45幢4/5楼 电话：

0575-85087896 (研发部)

传真：0575-88125157

E-mail: htw@uni-semic.com

无锡地址：无锡市锡山区先锋中路 6 号中国电子（无锡）数字芯城 1#综合楼 503室

电 话：0510-85297939

E-mail: zh@uni-semic.com

深圳地址：深圳市宝安区西乡街道南昌社区宝源路泳辉国际商务大厦410

电 话：0755-84510976

E-mail: htw@uni-semic.com